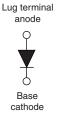
Vishay Semiconductors

High Performance Schottky Rectifier, 240 A



www.vishay.com



HALF-PAK (D-67)

PRODUCT SUMMARY				
I _{F(AV)}	240 A			
V _R	100 V			
Package HALF-PAK (D-67)				
Circuit	Single diode			

FEATURES

- 175 °C T_J operation
- · Low forward voltage drop
- High frequency operation
- · Guard ring for enhanced ruggedness and long term reliability
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION

The VS-243NQ.. high current Schottky rectifier module series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in high current switching power supplies, plating power supplies, UPS systems, converters, freewheeling diodes, welding, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
I _{F(AV)}	Rectangular waveform	240	А			
V _{RRM}		100	V			
I _{FSM}	t _p = 5 μs sine	25 500	А			
V _F	240 A _{pk} , T _J = 125 °C	0.72	V			
TJ	Range	-55 to +175	°C			

VOLTAGE RATINGS				
PARAMETER	SYMBOL	VS-243NQ100PbF	UNITS	
Maximum DC reverse voltage	V _R	100	V	
Maximum working peak reverse voltage	V _{RWM}	100	v	

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current See fig. 5	I _{F(AV)}	50 % duty cycle at T_{C} = 132 °C, rectangular waveform		240	
Maximum peak one cycle non-repetitive surge current		5 µs sine or 3 µs rect. pulse	Following any rated load condition and with	25 500	А
See fig. 7	'FSM	IFSM 10 ms sine or 6 ms rect. pulse rated V _{RRM} app		3300	
Non-repetitive avalanche energy	E _{AS}	T _J = 25 °C, I _{AS} = 5.5 A, L = 1 mH		15	mJ
Repetitive avalanche current	I _{AR}	Current decaying linearly to zero in 1 μ s Frequency limited by T _J maximum V _A = 1.5 x V _R typical		1	А

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ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop See fig. 1	V _{FM} ⁽¹⁾	240 A	T _J = 25 °C	0.95	V
		480 A		1.26	
		240 A	T _{.1} = 125 °C	0.72	
		480 A	1j = 125 0	0.85	
Maximum reverse leakage current See fig. 2	I _{RM}	T _J = 25 °C	$V_{\rm B} = Rated V_{\rm B}$	6	mA
		T _J = 125 °C	V _R = naleu V _R	80	
Maximum junction capacitance	CT	V_{R} = 5 V_{DC} (test signal range 100 kHz to 1 MHz) 25 °C		5500	pF
Typical series inductance	L _S	From top of terminal hole to mounting plane		5.0	nH
Maximum voltage rate of change	dV/dt	Rated V _R		10 000	V/µs

Note

⁽¹⁾ Pulse width = 500 μ s

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage tempera	ature range	T _J , T _{Stg}		-55 to +175	°C
Maximum thermal resistance, junction to case		R _{thJC}	DC operation 0.19		°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.05	
Approximate weight				30	g
				1.06	oz.
Mounting torgue	minimum			3 (26.5)	N ⋅ m (lbf ⋅ in)
	maximum		Non-lubricated threads	4 (35.4)	
Terminal torque	minimum		Non-lubricated threads	3.4 (30)	
	maximum			5 (44.2)	
Case style				HALF-PA	< module

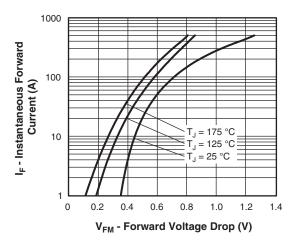


Fig. 1 - Maximum Forward Voltage Drop Characteristics

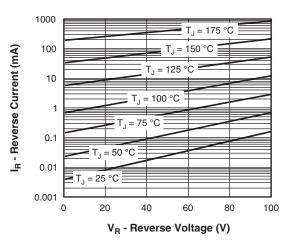


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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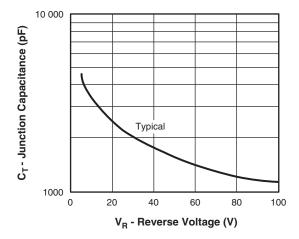


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

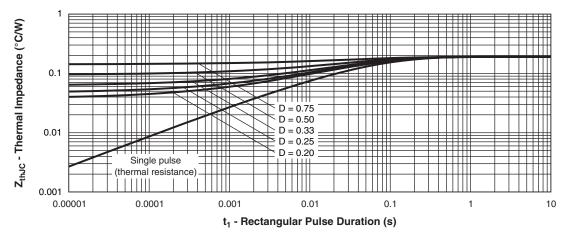


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

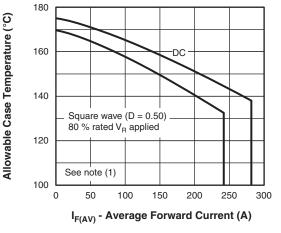


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

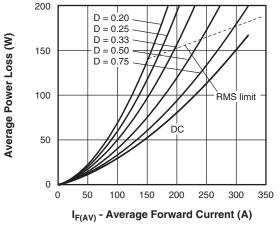


Fig. 6 - Forward Power Loss Characteristics

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VS-243NQ100PbF

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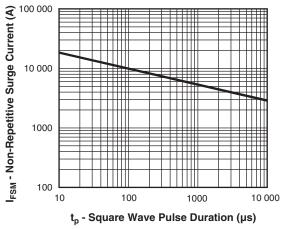


Fig. 7 - Maximum Non-Repetitive Surge Current

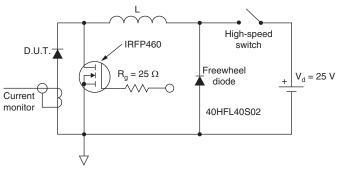
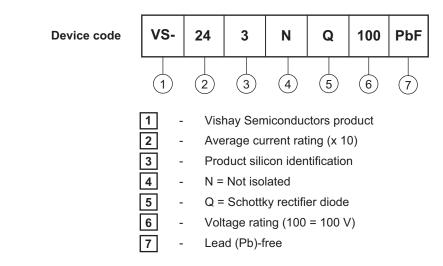


Fig. 8 - Unclamped Inductive Test Circuit

Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
 - $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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17.5 (0.69) 16.5 (0.65)



DIMENSIONS in millimeters (inches)

SHAY





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